

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	200.00 +/- 0.30 mm	
	2.0	Notch or Flat	Notch (SEMI Std)	Wafer Vendor
	3.0	Notch Direction	<110>+/-1	Wafer Vendor
	4.0	Overall Thickness	711.00 +/- 17.00 µm	ADE 100%
	5.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	6.0	Bow	<100.00µm	ADE to ASTM F534, 20% Best effort not guaranteed
	7.0	Warp	<100.00µm	ADE to ASTM F657, 20% Best effort not guaranteed
	8.0	Edge Chips	0	Bright Light, 100% (note 2)
	9.0	Edge Exclusion	5mm	
HandleSilicon	10.0	Handle Growth Method	CZ	Wafer Vendor
	11.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	12.0	Handle Thickness	650.00 +/- 15.00 µm	ADE, 100%
	13.0	Handle Doping Type	Any	Wafer Vendor
	14.0	Handle Dopant	Any	Wafer Vendor
	15.0	Handle Resistivity	>0.001 Ohm cm	Wafer Vendor
	16.0	Backside Finish	Polished with laser mark and oxide.	Guaranteed by process
BuriedOxide	17.0	Oxide Type	Thermal	
	18.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
DeviceSilicon	19.0	Device Growth Method	CZ	Wafer Vendor
	20.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	21.0	Nominal Thickness	60.00 +/- 1.00 µm	ADE single point - 100%
	22.0	Device Doping Type	Any	Wafer Vendor
	23.0	Device Dopant	Any	Wafer Vendor
	24.0	Device Resistivity	<0.005 Ohmcm	Wafer Vendor
	25.0	Voids	0	Bright Light, 100% (note 2)
	26.0	Scratches	0	Bright Light, 100% (note 2)
	27.0	Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information